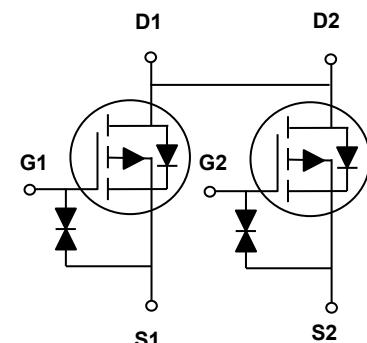


Main Product Characteristics

BV _{DSS}	-20V
R _{DS(ON)}	33mΩ
I _D	-5.6A



PPAK3X3



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFN8209 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±10	V
Drain Current – Continuous ($T_A=25^\circ\text{C}$)	I _D	-5.6	A
Drain Current – Continuous ($T_A=70^\circ\text{C}$)		-4.5	A
Drain Current –Pulsed ¹	I _{DM}	-22.4	A
Power Dissipation ($T_A=25^\circ\text{C}$)	P _D	1.67	W
Power Dissipation – Derate above 25°C		0.01	W/°C
Thermal Resistance Junction to Ambient	R _{θJA}	75	°C/W
Storage Temperature Range	T _{STG}	-55 to +150	°C
Operating Junction Temperature Range	T _J	-55 to +150	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	-	-	V
BV_{DSS} Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	Reference to 25°C , $I_{\text{D}}=-1\text{mA}$	-	-0.02	-	$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	-	-	-1	μA
		$V_{\text{DS}}=-16\text{V}, V_{\text{GS}}=0\text{V}, T_J=125^\circ\text{C}$	-	-	-10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 10\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics						
Static Drain-Source On-Resistance ²	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$	-	28	33	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-3\text{A}$	-	37	45	$\text{m}\Omega$
		$V_{\text{GS}}=-1.8\text{V}, I_{\text{D}}=-2\text{A}$	-	49	65	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}, I_{\text{D}}=-250\mu\text{A}$	-0.3	-0.6	-1	V
$V_{\text{GS}(\text{th})}$ Temperature Coefficient	$\Delta V_{\text{GS}(\text{th})}$		-	2	-	$\text{mV}/^\circ\text{C}$
Forward Transconductance	g_{fs}	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-3\text{A}$	-	8.5	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{2, 3}	Q_g	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$	-	16.1	25	nC
Gate-Source Charge ^{2, 3}	Q_{gs}		-	1.8	3.6	
Gate-Drain Charge ^{2, 3}	Q_{gd}		-	3.8	7	
Turn-On Delay Time ^{2, 3}	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=-10\text{V}, V_{\text{GS}}=-4.5\text{V}, R_{\text{G}}=25\Omega, I_{\text{D}}=1\text{A}$	-	8.2	16	nS
Rise Time ^{2, 3}	T_r		-	30	57	
Turn-Off Delay Time ^{2, 3}	$T_{\text{d}(\text{off})}$		-	71	135	
Fall Time ^{2, 3}	T_f		-	20	38	
Input Capacitance	C_{iss}		-	1440	2100	pF
Output Capacitance	C_{oss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	-	155	230	
Reverse Transfer Capacitance	C_{rss}		-	115	170	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_s	$V_G=V_D=0\text{V}$, Force Current	-	-	-5.6	A
Pulsed Source Current ²	I_{SM}		-	-	-11.2	A
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}, I_s=-1\text{A}, T_J=25^\circ\text{C}$	-	-	-1	V

Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. Pulsed tested: pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

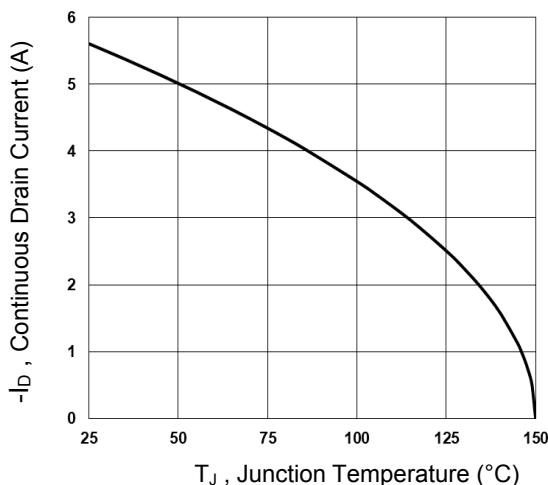


Figure 1. Continuous Drain Current vs. T_J

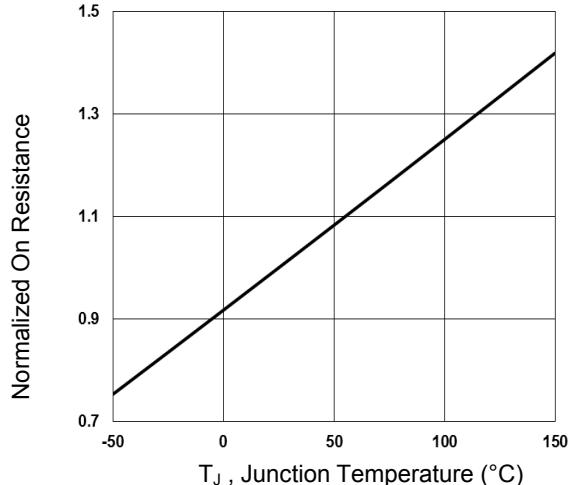


Figure 2. Normalized R_{DS(ON)} vs. T_J

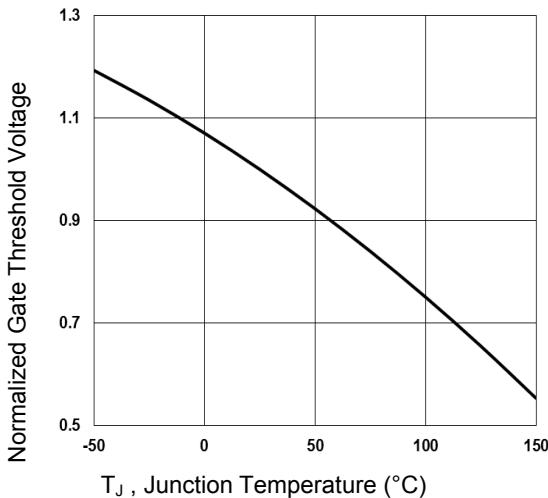


Figure 3. Normalized V_{th} vs. T_J

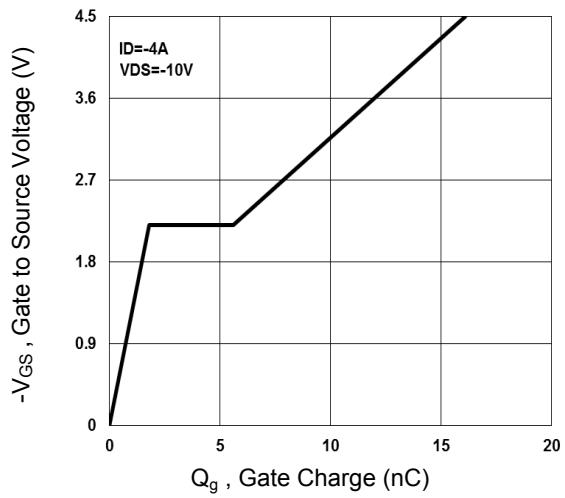


Figure 4. Gate Charge Waveform

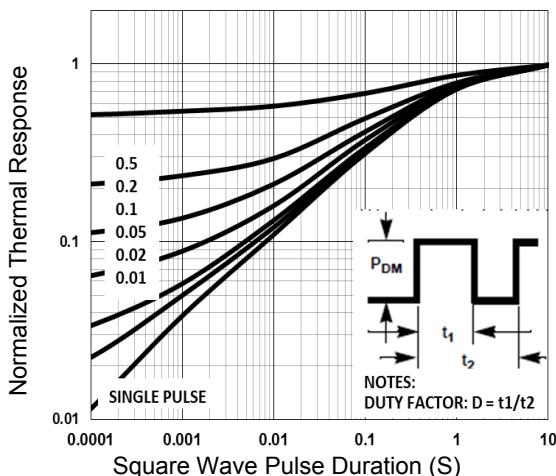


Figure 5. Normalized Transient Response

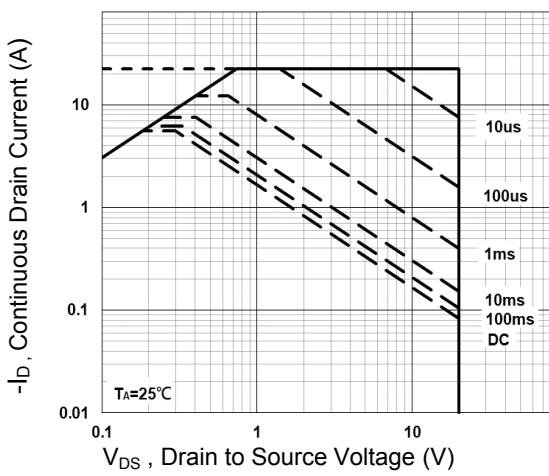


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

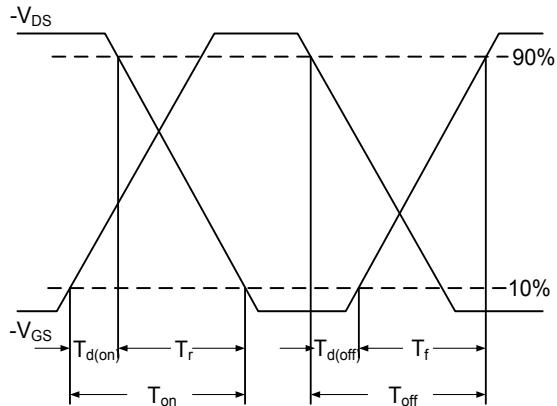


Figure 7. Switching Time Waveform

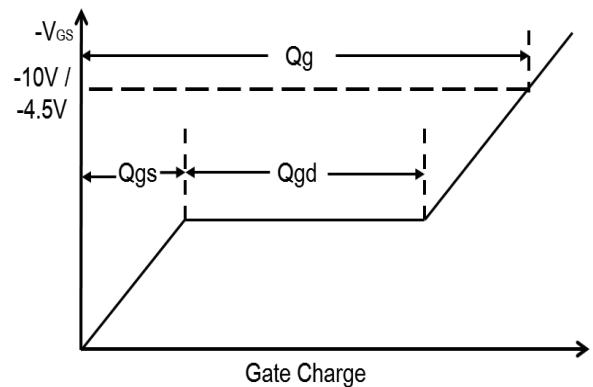
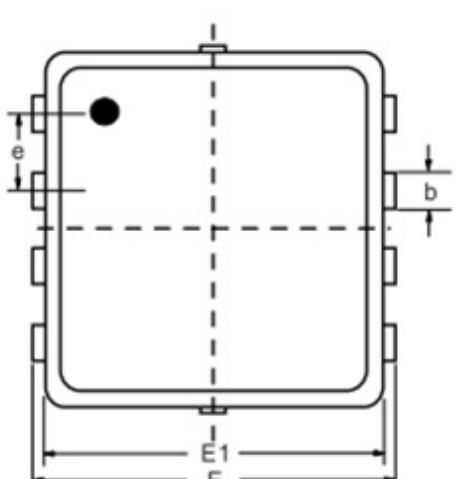


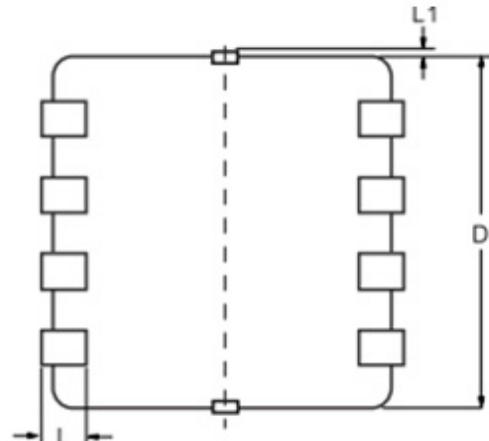
Figure 8. Gate Charge Waveform

Package Outline Dimensions

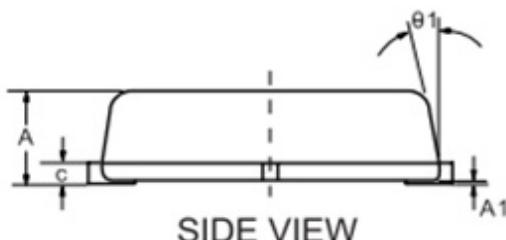
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TOP VIEW



BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.700	0.800	0.900
A1	0.000	-	0.050
b	0.250	0.300	0.350
c	0.080	0.152	0.250
D	2.800	2.900	3.000
E	2.700	2.800	2.900
E1	2.200	2.300	2.400
e	0.65BSC		
L	0.200	0.375	0.450
L1	0.00	-	0.10
Θ_1	0°	10°	12°